

TENTATIVE TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-MOS FET / PHOTO-TRANSISTOR

TLP270D

MOBILE / NOTE PCs

PDA's

MULTIMEDIA TV's

MODEMS

TLP270D has many multi-functions in DAA circuits for modems, which is a fully integrated design photocoupler in a 14pin (SOP16).

① Photorelay

Dial pulsing switch, Hookswitch

- 1 Form A
- Peak Off-State Voltage : 200 V (MIN.)
- Trigger LED Current : 3 mA (MAX.)
- On-State Current : 150 mA (MAX.)

② Photocoupler

Ring detection

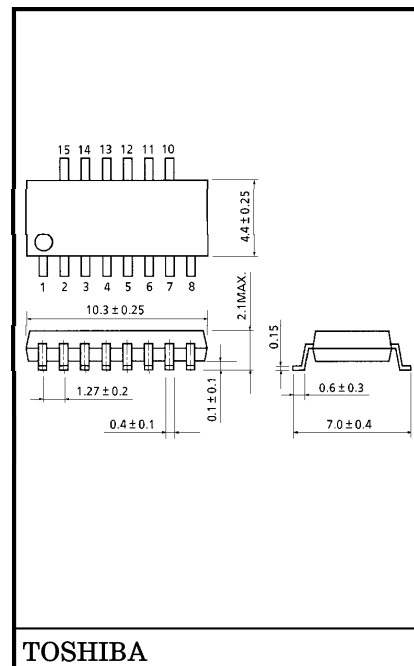
- Collector-Emitter Voltage : 80 V (MIN.)
- Current Transfer Ratio : 50% (MIN.)

③ Darlington Transistor

Electronic inductor

- Collector-Emitter Voltage : 30 V (MIN.)
- Collector Current : 150 mA (MAX.)

Unit in mm



Weight : 0.2 g

④ Bridge Rectifier

Polarity protection

- Reverse Voltage : 30 V (MIN.)
- Forward Voltage : 1.7 V (MAX.)

⑤ Zener Diode

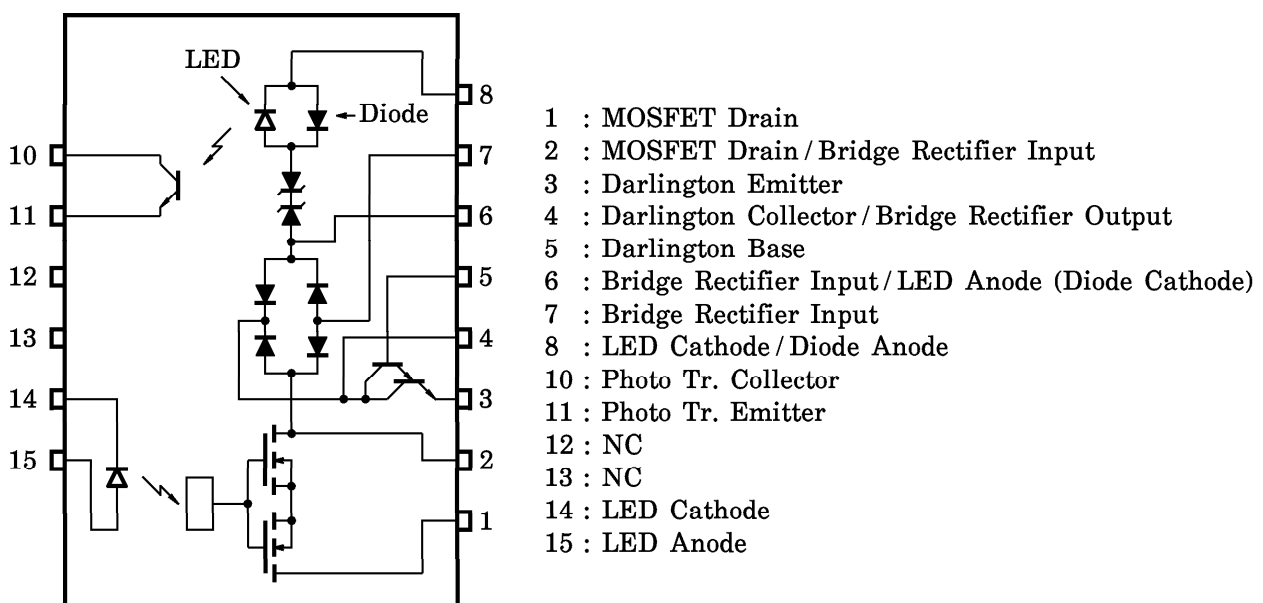
Ring detection protector

- Zener Voltage : 22~32 V

(Common)

- Isolation Voltage : 1500 Vrms (MIN.)
- UL Recognized : UL1577, File No. E67349

PIN CONFIGURATION (TOP VIEW)



PHOTORELAY (1-Form-A)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current	I _F	50	mA
	Forward Current Derating (Ta ≥ 25°C)	ΔI _F / °C	−0.5	mA / °C
	Peak Forward Current (100 μs pulse, 100 pps)	I _{FP}	1	A
	Reverse Voltage	V _R	5	V
	Junction Temperature	T _j	125	°C
DETECTOR	Off-State Output Terminal Voltage	V _{OFF}	200	V
	On-State RMS Current	I _{ON}	150	mA
	On-State RMS Current Derating (Ta ≥ 25°C)	ΔI _{ON} / °C	−1.5	mA / °C
	Junction Temperature	T _j	125	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
	Reverse Current	I _R	V _R = 5 V	—	—	10	μA
	Capacitance	C _T	V = 0, f = 1 MHz	—	30	—	pF
DETECTOR	Off-State Current	I _{OFF}	V _{OFF} = 200 V	—	—	1	μA
	Capacitance	C _{OFF}	V = 0, f = 1 MHz	—	90	—	pF

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Trigger LED Current	I _{FT}	I _{ON} = 150 mA	—	1	3	mA
On-State Resistance	R _{ON}	I _{ON} = 150 mA, I _F = 5 mA	—	5	8	Ω

SWITCHING CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Turn-on Time	t _{ON}	R _L = 200 Ω, V _{CC} = 20 V, I _F = 5 mA	—	—	1.5	ms
Turn-off Time	t _{OFF}		—	—	1	

PHOTOCOUPLER (AC-Input Transistor output)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current	I_F	± 50	mA
	Forward Current Derating (Ta $\geq 25^\circ\text{C}$)	$\Delta I_F / ^\circ\text{C}$	-0.5	mA / $^\circ\text{C}$
	Pulse Forward Current (100 μs pulse, 100 pps)	I_{FP}	1	A
	Junction Temperature	T_j	125	$^\circ\text{C}$
DETECTOR	Collector-Emitter Voltage	V_{CEO}	80	V
	Emitter-Collector Voltage	V_{ECO}	7	V
	Collector Current	I_C	50	mA
	Collector Power Dissipation (1 Circuit)	P_C	150	mW
	Collector Power Dissipation Derating (Ta $\geq 25^\circ\text{C}$) (1 Circuit)	$\Delta P_C / ^\circ\text{C}$	-1.5	mW / $^\circ\text{C}$
	Junction Temperature	T_j	125	$^\circ\text{C}$

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = \pm 10 \text{ mA}$	1.0	1.15	1.3	V
	Capacitance	C_T	$V = 0, f = 1 \text{ MHz}$	—	60	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C = 0.5 \text{ mA}$	80	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR) ECO}$	$I_E = 0.1 \text{ mA}$	7	—	—	V
	Collector Dark Current	I_D	$V_{CE} = 48 \text{ V}$ (Ambient Light : 100 lx)	—	0.01 (2)	0.1 (20)	μA
			$V_{CE} = 48 \text{ V}, T_a = 85^\circ\text{C}$ (Ambient Light : 100 lx)	—	2 (4)	50 (50)	μA
	Capacitance	C_{CE}	$V = 0, f = 1 \text{ MHz}$	—	10	—	pF

COUPLED ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio (CTR)	I_C / I_F	$I_F = 5 \text{ mA}$, $V_{CE} = 5 \text{ V}$ Rank GB	50	—	—	%
			100	—	—	
Saturated CTR	I_C / I_F (sat)	$I_F = 1 \text{ mA}$, $V_{CE} = 0.4 \text{ V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-Emitter Saturation Voltage	$V_{CE}(\text{sat})$	$I_C = 2.4 \text{ mA}$, $I_F = 8 \text{ mA}$	—	—	0.4	V
		$I_C = 0.2 \text{ mA}$, $I_F = 1 \text{ mA}$ Rank GB	—	0.2	—	
			—	—	0.4	
Off-State Collector Current	$I_C(\text{off})$	$V_F = 0.7 \text{ V}$, $V_{CE} = 48 \text{ V}$	—	—	10	μA

SWITCHING CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	t_r	$V_{CC} = 10 \text{ V}$, $I_C = 2 \text{ mA}$, $R_L = 100 \Omega$	—	2	—	μs
Fall Time	t_f		—	3	—	
Turn-on Time	t_{on}		—	3	—	
Turn-off Time	t_{off}		—	3	—	
Turn-on Time	t_{ON}	$R_L = 1.9 \text{ k}\Omega$, $V_{CC} = 5 \text{ V}$, $I_F = 16 \text{ mA}$	—	2	—	
Storage Time	t_s		—	25	—	
Turn-off Time	t_{OFF}		—	40	—	

ZENER DIODEINDIVIDUAL ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Zener Voltage	V_Z	—	22	27	32	V

DARLINGTON TRANSISTOR

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	30	V
Collector-Emitter Voltage	V _{CEO}	30	V
Emitter-Base Voltage	V _{EBO}	10	V
Collector Current	I _C	0.15	A
Base Current	I _B	20	mA
Collector Power Dissipation	P _C	350	mW
Junction Temperature	T _j	125	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Off Current		I _{CBO}	V _{CB} = 30 V, I _E = 0	—	—	10	μA
Emitter Off Current		I _{EBO}	V _{EB} = 10 V, I _C = 0	—	—	10	μA
Collector-Emitter Breakdown Voltage		V _(BR) CEO	I _C = 10 mA, I _B = 0	30	—	—	V
DC Current Gain		h _{FE}	V _{CE} = 2 V, I _C = 150 mA	4000	—	—	
Collector-Emitter Saturation Voltage		V _{CE (sat)}	I _C = 0.15 A, I _B = 1 mA	—	—	1.5	V
Switching Time	Turn-on Time	t _{on}	I _B = 1 mA, V _{CC} = 15 V, R _L = 15 Ω	—	0.20	—	μs
	Storage Time	t _{stg}		—	0.6	—	
	Fall Time	t _f		—	0.3	—	

BRIDGE RECTIFIER

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Repetitive Peak Reverse Voltage	V _{RRM}	30	V
Average Output Rectified Current	I _O	0.15	A
Peak One Cycle Surge Forward Current	I _{FSM}	0.5	A
Junction Temperature	T _j	125	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V _{FM}	I _{FM} = 0.12 A	—	—	1.7	V
Repetitive Peak Reverse Current	I _{RRM}	V _{RRM} = Rated	—	—	10	μA

PACKAGE (Common)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Total Package Power Dissipation	P _T	650	mW
Storage Temperature Range	T _{stg}	−55~100	°C
Operating Temperature Range	T _{opr}	−20~85	°C
Lead Soldering Temperature (10 s)	T _{sol}	260	°C
Isolation Voltage (AC, 1 min., R.H. ≤ 60%) (Note 1)	BV _S	1500	V _{rms}

(Note 1) : Device considered a two-terminal device : Pins 1,
2, 3, 4, 5, 6, 7 and 8 shorted together and pins
10, 11, 12, 13, 14 and 15 shorted together.

ISOLATION CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance Input to Output	C _S	V _S = 0, f = 1 MHz	—	0.8	—	pF
Isolation Resistance	R _S	V _S = 500 V, R.H. ≤ 60%	5 × 10 ¹⁰	10 ¹⁴	—	Ω
Isolation Voltage	BV _S	AC, 1 minute	1500	—	—	V _{rms}
		AC, 1 second, in oil	—	3000	—	
		DC, 1 minute, in oil	—	3000	—	V _{dc}

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